

CAPPING COATING FOR 3D INTEGRATION APPLICATIONS

ABSTRACT OF THE DISCLOSURE

A structure for a semiconductor component is provided having a bi-layer capping coating integrated and built on supporting layer to be transferred. The bi-layer capping protects the layer to be transferred from possible degradation resulting from the attachment and removal processes of the carrier assembly used for layer transfer. A wafer-level layer transfer process using this structure is enabled to create three-dimensional integrated circuits.